

# Spontaneous currents and half-integer Shapiro steps in Superconductor-Ferromagnet-Superconductor 0- Josephson junctions

S. M. Frolov and D. J. Van Harlingen

Department of Physics, University of Illinois at Urbana-Champaign, Urbana, IL, 61801, USA

V. V. Bolginov, V. A. Oboznov, and V. V. Ryazanov

Institute of Solid State Physics, Russian Academy of Sciences, Chernogolovka, 142432, Russia

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We study Superconductor-Ferromagnet-Superconductor (Nb-Cu<sub>0.47</sub>Ni<sub>0.53</sub>-Nb) Josephson junctions with spatial variations in the barrier thickness. Critical current vs. magnetic flux diffraction patterns indicate that the critical current density changes sign along the width of the junctions, creating interfaces between 0 and  $\pi$  junction regions around which spontaneous currents can circulate. Shapiro steps observed at half-integer Josephson voltages can be explained by the phase-locking of the spontaneous circulating currents to the applied rf modulation.

In the past few years considerable attention has been directed toward the understanding and realization of Josephson junctions [1]. Transitions between 0 and  $\pi$  junction states were demonstrated in Superconductor-Ferromagnet-Superconductor (SFS) junctions as a function of temperature [2] and barrier thickness [3], and in mesoscopic Superconductor-Normal metal-Superconductor (SNS) junctions as a function of the barrier thermalization voltage [4]. In both systems, the first-order Josephson supercurrent vanishes at the 0- $\pi$  transition, making the transition region feasible for the observation of second-order Josephson tunneling characterized by a  $\sin(2\phi)$  component in the current-phase relation (CPR). Period doubling in the critical current  $I_c$  vs. magnetic flux patterns of dc SQUIDs incorporating two mesoscopic SNS junctions, one biased at the 0- $\pi$  transition, has been attributed to a second-order Josephson component [5]. In SFS junctions, Shapiro steps at half-integer Josephson voltages were reported close to a temperature minimum in  $I_c$ , consistent with a  $\sin(2\phi)$  Josephson component [6]. However, direct measurements of the CPR in uniform SFS junctions revealed no discernible  $\sin(2\phi)$  term [7].

In this paper, we present experimental evidence that half-integer Shapiro steps in the current-voltage characteristics can occur in SFS junctions with a non-uniform critical current density without the need for an intrinsic  $\sin(2\phi)$  component. In our junctions, we observe half-integer Shapiro steps, but only in a narrow temperature range close to the temperature at which a deep but finite minimum occurs in the zero-field critical current. In this regime, we find that part of the junction is in the 0 state and part is in the  $\pi$  state with the net critical currents of the two regions comparable in magnitude, and that the energy of the junction is minimized by generation of a spontaneous circulating current. This current can couple to the applied microwave field, producing half-integer Shapiro steps. A similar effect has been observed in an analogous system, a nearly-symmetric dc SQUID with an

applied magnetic flux of  $\frac{1}{2}\phi_0$  ( $\phi_0 = h/2e$ ) [8].

A Josephson junction is characterized by a negative critical current. The mechanism of the  $\pi$  state in SFS Josephson junctions is the spatial oscillation of the proximity-induced order parameter inside the ferromagnetic barrier which arises from its exchange field [9]. The critical current density  $J_c$  is predicted to oscillate and decay with the barrier thickness  $d$  according to [10]

$$J_c(d) = J_{c0} \cos \frac{d}{F_2} + \frac{F_1}{F_2} \sin \frac{d}{F_2} \exp \left( -\frac{d}{F_1} \right); \quad (1)$$

where  $F_1$  is the decay length and  $2/F_2$  is the oscillation period of the order parameter. This expression is valid for  $d \ll F_1$ . The lengths  $F_1$  and  $F_2$  can be extracted by fitting the measured  $J_c(d)$  to Eq. (1). In our junctions at  $T = 4.2$  K,  $F_1 = 1.3$  nm and  $F_2 = 3.7$  nm, and the first two nodes of  $J_c$  occur for  $d = 11$  nm and  $d = 22$  nm. The lengths  $F_1$  and  $F_2$  vary with temperature according to

$$\frac{F_{1,2}(T)}{F_{1,2}(0)} = \frac{(E_{ex} - E_F)}{[(k_B T)^2 + E_{ex}^2]^{1/2}}; \quad (2)$$

where  $E_{ex}$  is the ferromagnetic exchange energy and  $F_{1,2}(0)$  are the values at zero temperature. By using a weakly-ferromagnetic alloy Cu<sub>0.47</sub>Ni<sub>0.53</sub> with  $T_{Curie} = 60$  K as a barrier material, temperature changes in the 1-4 K range have a significant effect on the suppression and modulation of the induced pair correlations in the ferromagnetic interlayer, allowing us to tune through the 0- $\pi$  transition by changing the temperature.

The SFS junctions were patterned by optical lithography. Base and counterelectrode superconducting layers were dc-sputtered Nb with thicknesses 100 nm and 240 nm respectively, separated by an 11 nm barrier layer of rf-sputtered Cu<sub>0.47</sub>Ni<sub>0.53</sub> and a 20-30 nm layer of dc-sputtered Cu. The ferromagnetic layer thickness is chosen near the first 0- $\pi$  transition thickness, while the Cu

layer protects the barrier during processing. Junction sizes were  $4\text{ }\mu\text{m} \times 4\text{ }\mu\text{m}$  or  $10\text{ }\mu\text{m} \times 10\text{ }\mu\text{m}$ , defined by a window in an insulating SiO<sub>2</sub> layer deposited on top of the CuNi/Cu barrier. Because SFS junctions have small  $I_c R_N$  products  $\sim 1\text{--}100\text{ nV}$ , a commercial dc SQUID with a standard resistor  $R_{st} = 10\text{ }\mu\Omega$  is used as a potentiometer with sensitivity  $1\text{ pV}$  to perform transport measurements. This translates into a critical current measurement resolution of  $100\text{ nA}$ . A uniform magnetic field up to  $100\text{ G}$  can be applied through the junction barrier from a solenoid coil to measure the magnetic field dependence of the critical current, and an rf current component at frequencies  $f_{rf} = 0.3\text{--}1.3\text{ MHz}$  is superimposed with the dc bias current to observe ac-induced Shapiro steps in the current-voltage characteristics.

Measurements of the critical current  $I_c$  vs. the applied magnetic flux threading the junction barrier reveal that the critical current distribution is often not uniform across the junction. Figure 1(b) shows a series of  $I_c(\Phi)$  curves in the temperature range  $1.4\text{--}4.2\text{ K}$  for a  $10\text{ }\mu\text{m} \times 10\text{ }\mu\text{m}$  junction. At  $T = 4.2\text{ K}$ ,  $I_c(\Phi)$  has a Fraunhofer-like shape but with non-vanishing supercurrents at the side minima. This can occur in a junction with a localized region of high critical current density. In the temperature interval  $1.4\text{--}1.9\text{ K}$  a minimum in the critical current is observed at zero field, indicating that

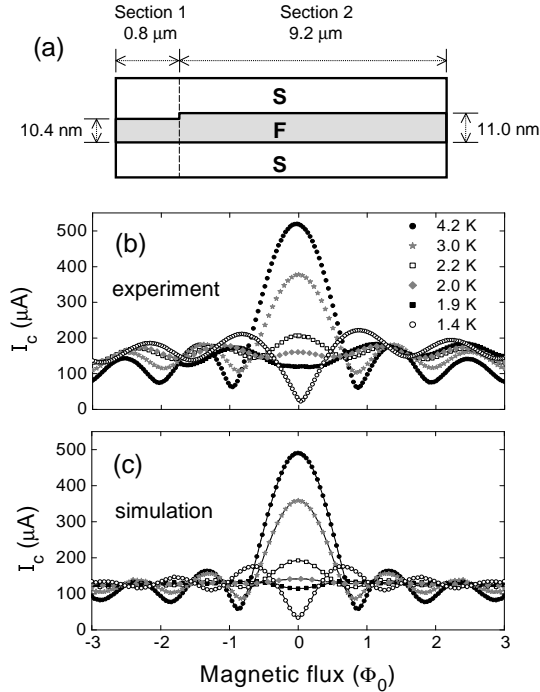


FIG. 1: (a) Stepped ferromagnetic barrier deduced from critical current vs. applied magnetic flux measurements. (b) Diffraction patterns at a series of temperatures showing deviations from Fraunhofer behavior at low temperatures. (c) Simulated diffraction patterns using the deduced ferromagnetic barrier profile.

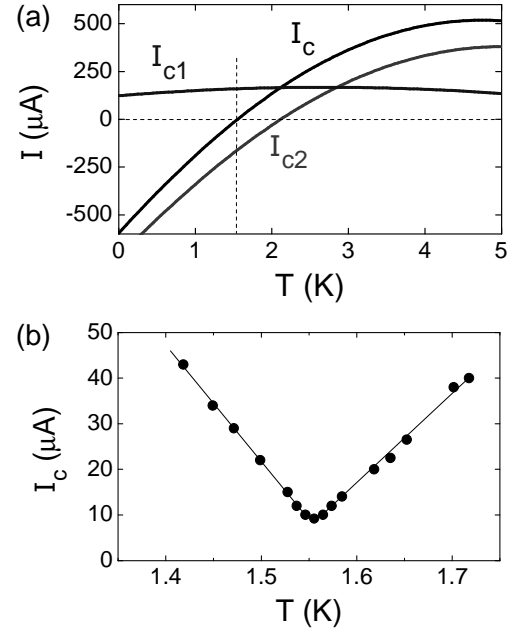


FIG. 2: (a) Calculated temperature variation of the critical current for junction sections 1 and 2 and for the entire junction. The thin region remains in the 0 state at all temperatures while the thick region crosses from the 0 state into the state. (b) Measured critical current vs. temperature at zero applied magnetic field but remains finite.

regions of opposite polarity critical current density exist in the junction.

The temperature evolution of the  $I_c(\Phi)$  patterns indicates that some fraction of the junction width makes a transition from the 0 state to the state as the temperature is lowered, while the remaining part stays in the 0 state. The critical current non-uniformity likely arises from spatial variations in the barrier thickness across the junction but could also be caused by inhomogeneities in the ferromagnetic exchange energy or by variations in the S-F interface transparency. Figure 1(a) shows the step barrier geometry deduced by fitting the measured diffraction patterns in Fig. 1(b) in the short junction approximation in which magnetic fields from the tunneling current are neglected. We obtain good agreement as demonstrated in Fig. 1(c). It is not surprising that the small  $6\text{ }\mu\text{m}$  step has such a dramatic effect on the diffraction patterns since close to the 0- transition the critical current density in our junctions changes by  $1000\text{ A/cm}^2$  per  $1\text{ nm}$  change in the barrier thickness. For the barrier profile in Fig. 1(a) and the experimental data for  $J_c$  (d), we use Eqs. (1) and (2) to calculate the temperature dependences of the zero-field critical currents  $I_{c1}$  of the thin narrow region,  $I_{c2}$  of the wide thick region, and  $I_c$ , the total junction critical current. These are plotted in Fig. 2(a). We see that  $I_{c1}$  is relatively constant while  $I_{c2}$  decreases and changes sign at  $T \approx 2.1\text{ K}$ , causing the  $I_c$  to vanish at  $T_0 \approx 1.55\text{ K}$ . However, measurements

plotted in Fig. 2(b) show that  $I_c(\phi = 0)$  does not go fully to zero at  $T_0$ , instead reaching a minimum value of  $\sim 10 \text{ A}$ .

Shapiro steps induced in zero applied magnetic field at drive frequency  $f_{rf}$  are also anomalous, exhibiting not only the usual steps at integer multiples of the Josephson voltage  $V_n = n(hf_{rf}/2e)$ , but also steps at half-integer Josephson voltages such as  $V_{1/2} = hf_{rf}/4e$  and  $V_{3/2} = 3hf_{rf}/4e$  when the temperature is close to  $T_0$ . An example is given in Fig. 3(a) for  $f_{rf} = 1.3 \text{ MHz}$ . Figure 3(b) shows the maximum value of the ( $V = 0$ ) Josephson supercurrent, and the maximum amplitudes of the  $n = \frac{1}{2}$  and the  $n = 1$  Shapiro steps obtained by adjusting the rf amplitude (the  $n^{\text{th}}$  step amplitudes vary with rf voltage  $V_{rf}$  according to the corresponding Bessel functions  $J_n(2eV_{rf}/hf_{rf})$  as expected). At temperatures far from  $T_0$ , only integer Shapiro steps were observed. Half-integer steps appear near the minimum in the critical current in a temperature range of width  $\sim 60 \text{ mK}$ . Note that this minimum in the critical current measured in Fig. 3(b) is about  $25 \text{ mK}$  lower than that in Fig. 2(b) as a result of room-temperature annealing of the ferromagnetic barrier during the 3 days between when the measurements were made [2]. In other junctions in which the critical current does vanish at  $T_0$ , half-integer Shapiro steps were not observed at any temperatures.

The non-vanishing critical current at  $T_0$  and half-integer Shapiro steps could result from a  $\sin(2\phi)$  component present in the current-phase relation near the  $0-\pi$  transition. However, we believe that they are more readily explained by self-field effects that must be taken into account in finite width  $0-\pi$  junctions. At temperatures close to  $T_0$ , spontaneous currents circulate around interfaces between  $0$  and  $\pi$  regions to lower the total energy of the system [11, 12]. These circulating currents generate magnetic flux through the junction that prevent the total critical current from vanishing at any applied magnetic field. In addition, they can resonate with an rf bias current applied at twice the Josephson frequency, resulting in half-integer Shapiro steps. A detailed calculation of the spatial distribution of spontaneous currents and the net critical current in this regime requires a self-consistent solution of the Sine-Gordon equations in the junction. Computation of the amplitudes of the half-integer Shapiro steps further requires numerical simulations of the junction phase dynamics. However, we can understand the onset and effects of the spontaneous currents in a  $0-\pi$  junction in analogy to a dc SQUID with finite geometric inductance.

We consider a dc SQUID with a  $0$  junction of critical current  $I_{c0} > 0$  and a  $\pi$  junction of critical current  $I_c < 0$  in a loop of inductance  $L$ . In such a SQUID, phase coherence around the SQUID loop precludes both junctions being in their low energy states and the junction phases  $\phi_0$  and  $\phi_\pi$  depend on the inductance parameter  $L = 2LI_c = \phi_0$ , where  $I_c = (I_{c0} + I_c)/2$ , and

the critical current asymmetry  $\phi_0 = (I_{c0} - I_c)/2I_c$ . For  $L < 2 = (1 - \phi_0^2)$ , it is energetically favorable to switch the phase of the junction with the smaller critical current magnitude into its high energy state, e.g. if  $I_{c0} > I_c$ , then  $\phi_0 = \pi$ . Under the influence of a harmonic ac-drive,  $\phi_0$  and  $\phi_\pi$  wind in phase and only integer Shapiro steps can be observed. When  $L > 2 = (1 - \phi_0^2)$ , the SQUID energy is lowered by generation of a spontaneous circulating current and  $\phi_0 \neq \pi$ . In this regime, the phase differences  $\phi_0$  and  $\phi_\pi$  are no longer synchronized. Hence, the spontaneous circulating current  $J = (I_c - I_{c0})/\phi_0$  can phase-lock to the driving frequency in such a way that it switches direction an even or odd number of times during each period of the drive signal, corresponding to integer or half-integer Shapiro steps. This phenomenon has previously been studied in an equivalent system, an ordinary dc SQUID with an applied flux of  $\frac{1}{2}\phi_0$ . Measurements and simulations showed half-integer Shapiro steps with amplitudes that increase as the SQUID inductance is increased and the critical current asymmetry is decreased [8].

In a  $0-\pi$  junction, the existence of spontaneous circulating currents, and hence half-integer Shapiro steps, depends on the ratio of the widths of the  $0$  and  $\pi$  re-

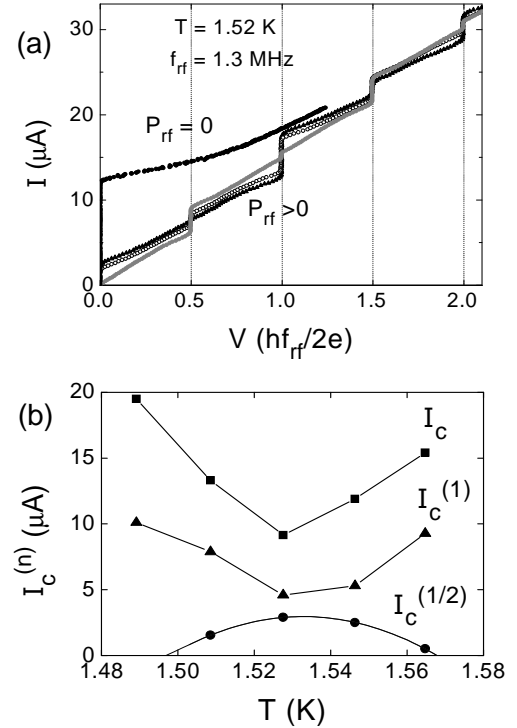


FIG. 3: (a) Current-voltage characteristics showing rf-induced Shapiro steps both at the usual voltages  $nhf_{rf}/2e$  and at half-integer values  $nhf_{rf}/4e$ . (b) Temperature dependence of the maximum (power-optimized) critical current steps, showing that the integer steps scale with the junction critical current whereas the half-integer steps only occur at temperatures near the minimum in the critical current.

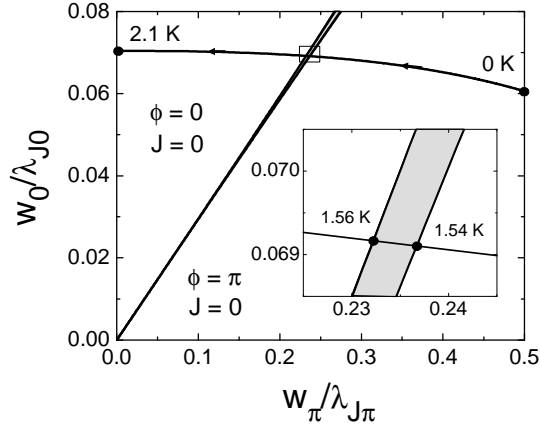


FIG. 4: Phase diagram mapping the region of  $w_0 = j_0$  and  $w = j$  values for which a spontaneous circulating current flows around the 0-step edge. In the shaded region, the phase drop across the junction and current density  $J$  vary spatially along the junction width. Outside this region, the phase is uniform with value 0 or  $\pi$  and no spontaneous currents flow in the junction.

gions of the junction  $w_0$  and  $w$  to their corresponding Josephson penetration depths  $j_0$  and  $j$  [11]. Here,  $j = (\hbar/2e_0 d_m J_c)^{1/2}$ , where the magnetic barrier thickness  $d_m = 2 + d$  depends on the penetration depth of the superconductor and the barrier thickness  $d$ . The phase diagram denoting the regimes of uniform phase and spontaneous current flow is shown in Fig. 4. Regimes with uniform phase differences  $\phi = 0$  or  $\pi$  are separated by a narrow region in which the phase differences vary across the junction due to spontaneous circulating currents. The circulating currents onset along lines defined by  $j \tanh(w_0 = j_0) = j_0 \tanh(w = j)$  and  $j_0 \tanh(w = j) = j \tanh(w_0 = j_0)$  [11]. Also shown is the path in the phase diagram followed by the non-uniform junction described in Fig. 2(a), for which  $d_m = 100$  nm, as the temperature is varied from 0 K to 2.1 K, the temperature at which the wide segment of the junction crosses into the 0 state. We see in the inset that spontaneous currents occur only in a narrow temperature range from 1.54–1.56 K. This is comparable to the temperature range from 1.50–1.56 K in which we observe half-integer Shapiro steps, suggesting that they have the same origin. Other non-uniform junctions that we have measured either had smaller areas so that  $w_0$  and  $w$  were smaller, or smaller barrier thickness steps so that  $j_0$  and  $j$  were larger. In either case, the temperature range of spontaneous currents was predicted to be immeasurably small ( $< 1$  mK), explaining why we were not able to observe half-integer Shapiro steps or a finite minimum critical current in these junctions.

Previously, we directly measured the current-phase relation of uniform SFS junctions with thicker barriers  $d = 22$  nm, close to the second node of the  $I_c(d)$  dependence,

and did not observe any signature of a  $\sin(2\phi)$  component in the Josephson tunneling [7]. This is in agreement with microscopic predictions that the second-order Josephson tunneling probability falls off more rapidly with increasing barrier thickness than the first-order Josephson effect [13, 14, 15]. Thus, to determine definitively whether or not a  $\sin(2\phi)$  component is present in the current-phase relation, uniform SFS Josephson junctions with barrier thicknesses  $d \approx 11$  nm close to the first node of  $I_c(d)$  should be studied. Simultaneous observation of Shapiro steps at half-integer Josephson voltages and period doubling in the current-phase relation in uniform SFS junctions is required to reliably verify the presence of a microscopic  $\sin(2\phi)$  component.

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